# BLC8G27LS-140AV

# Power LDMOS transistor Rev. 4 — 24 May 2017

**AMMPLEON** 

Product data sheet

#### **Product profile** 1.

#### 1.1 General description

140 W LDMOS packaged asymmetrical Doherty power transistor for base station applications at frequencies from 2496 MHz to 2690 MHz.

#### **Typical performance**

Typical RF performance at  $T_{case}$  = 25 °C in a Doherty demo board.

Test signal	f	V <sub>DS</sub>	P <sub>L(AV)</sub>	G <sub>p</sub>	$\eta_D$	ACPR
	(MHz)	(V)	(W)	(dB)	(%)	(dBc)
1-carrier W-CDMA	2496 to 2690	28	28	15	46	-30 <u>[1]</u>

<sup>[1]</sup> Test signal: 3GPP test model 1; 1 to 64 DPCH; PAR = 7.2 dB at 0.01 % probability on CCDF.

#### 1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low thermal resistance providing excellent thermal stability
- Decoupling leads to enable improved video bandwidth
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent pre-distortability
- Internally matched for ease of use
- Integrated ESD protection
- Compliant to Restriction of Hazardous Substances (RoHS) Directive 2002/95/EC

#### 1.3 Applications

■ RF power amplifier for LTE base stations and multi carrier applications in the 2496 MHz to 2690 MHz frequency range

## 2. Pinning information

Table 2. Pinning

Pin	Description		Simplified outline	Graphic symbol
1	drain1 (main)			
2	drain2 (peak)		5 1 2 6	1, 5
3	gate1 (main)			3_
4	gate2 (peak)		7	7
5	video decoupling (main)			47
6	video decoupling (peak)		3 4	2, 6
7	source	[1]		aaa-007731

<sup>[1]</sup> Connected to flange.

## 3. Ordering information

Table 3. Ordering information

Type number	Packag	ackage					
	Name	Description	Version				
BLC8G27LS-140AV	-	air cavity plastic earless flanged package; 6 leads	SOT1275-1				

## 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage		-	65	V
$V_{GS}$	gate-source voltage		-0.5	+13	V
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	225	°C

Continuous use at maximum temperature will affect the reliability, for details refer to the online MTF calculator.

## 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{\text{th(j-case)}}$	thermal resistance from junction to case	$T_{case}$ = 80 °C; $V_{DS}$ = 28 V; $I_{Dq}$ = 320 mA; $V_{GS(amp)peak}$ = 0.6 V		
		P <sub>L</sub> = 28 W	0.371	K/W
		P <sub>L</sub> = 80 W	0.221	K/W

#### 6. Characteristics

Table 6. DC characteristics

 $T_i$  = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Main dev	rice					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 0.72 \text{ mA}$	65	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 72 mA	1.5	1.9	2.3	V
$V_{GSq}$	gate-source quiescent voltage	V <sub>DS</sub> = 28 V; I <sub>D</sub> = 432 mA	1.6	2.1	2.4	V
I <sub>DSS</sub>	drain leakage current	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 28 V	-	-	1.4	μА
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	14	-	Α
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 11 V; V <sub>DS</sub> = 0 V	-	-	140	nA
9 <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 72 mA	-	0.60	-	S
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 2.52 \text{ A}$	-	205	323	mΩ
Peak dev	rice					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 1.1 \text{ mA}$	65	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 110 mA	1.5	1.9	2.3	V
$V_{GSq}$	gate-source quiescent voltage	V <sub>DS</sub> = 28 V; I <sub>D</sub> = 660 mA	1.6	2.0	2.4	V
I <sub>DSS</sub>	drain leakage current	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 28 V	-	-	1.4	μΑ
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	20	-	Α
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 11 V; V <sub>DS</sub> = 0 V	-	-	140	nA
9 <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 110 mA	-	0.97	-	S
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 3.85 \text{ A}$	-	145	215	mΩ

#### Table 7. RF characteristics

Test signal: 1-carrier W-CDMA; PAR = 7.2 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 1 to 64 DPCH;  $f_1$  = 2496 MHz;  $f_2$  = 2690 MHz; RF performance at  $V_{DS}$  = 28 V;  $I_{Dq}$  = 320 mA (main);  $V_{GS(amp)peak}$  = 0.6 V;  $T_{case}$  = 25 °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at 2496 MHz to 2690 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
G <sub>p</sub>	power gain	P <sub>L(AV)</sub> = 28 W	13.3	14.5	-	dB
RLin	input return loss	P <sub>L(AV)</sub> = 28 W	-	-10	-6	dB
$\eta_{D}$	drain efficiency	P <sub>L(AV)</sub> = 28 W	38	43	-	%
ACPR	adjacent channel power ratio	P <sub>L(AV)</sub> = 28 W	-	-33	-28	dBc

#### Table 8. RF characteristics

Test signal: pulsed CW;  $t_p$  = 100  $\mu$ s;  $\delta$  = 10 %; f = 2690 MHz; RF performance at  $V_{DS}$  = 28 V;  $I_{Dq}$  = 320 mA (main);  $V_{GS(amp)peak}$  = 0.6 V;  $T_{case}$  = 25 °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at 2496 MHz to 2690 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
L(GGD)	output power at 3 dB gain compression		119	148	178	W

#### 7. Test information

#### 7.1 Ruggedness in Doherty operation

The BLC8G27LS-140AV is capable of withstanding a load mismatch corresponding to a VSWR = 10 : 1 through all phases under the following conditions:  $V_{DS}$  = 28 V;  $I_{Dq}$  = 320 mA (main);  $V_{GS(amp)peak}$  = 0.6 V;  $P_L$  = 120 W (CW); f = 2496 MHz.

#### 7.2 Impedance information

Table 9. Typical impedance of main device

Measured load-pull data of main device;  $I_{Dq}$  = 450 mA (main);  $V_{DS}$  = 28 V.

f	Z <sub>S</sub> [1]	Z <sub>L</sub> [1]	P <sub>L</sub> [2]	η <sub>D</sub> [2]	G <sub>p</sub> [2]
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)
Maximum pov	ver load				
2500	3.29 – j6.00	2.69 – j7.69	86.89	58.88	15.02
2600	2.73 – j6.90	2.70 – j7.69	82.22	56.91	15.92
2700	7.30 – j7.07	2.69 – j8.29	82.41	54.82	15.56
Maximum dra	in efficiency load				
2500	3.29 – j6.00	3.83 – j6.95	75.75	63.55	16.26
2600	2.73 – j6.90	3.99 – j5.62	59.73	62.15	17.97
2700	7.30 – j7.07	1.69 – j4.80	38.38	61.19	18.44

<sup>[1]</sup>  $Z_S$  and  $Z_L$  defined in Figure 1.

Table 10. Typical impedance of peak device

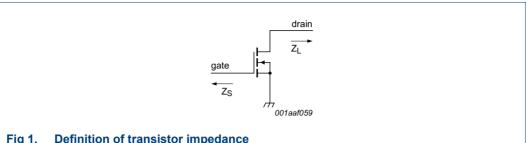
Measured load-pull data of peak device;  $I_{Dq}$  = 600 mA (peak);  $V_{DS}$  = 28 V.

f	Z <sub>S</sub> [1]	Z <sub>L</sub> [1]	P <sub>L</sub> [2]	η <sub>D</sub> [2]	G <sub>p</sub> [2]
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)
Maximum	power load			,	
2500	3.45 – j8.09	4.95 – j9.05	127.31	55.27	15.24
2600	4.39 – j7.53	6.05 – j9.94	123.54	54.54	15.69
2700	6.42 – j7.43	7.21 – j9.74	115.39	55.81	15.83
Maximum	drain efficiency loa	d			
2500	3.45 – j8.09	3.99 - j5.62	93.91	61.09	17.18
2600	4.39 – j7.53	4.24 – j6.14	93.95	62.64	17.71
2700	6.42 – j7.43	4.46 – j6.75	86.88	61.05	17.23

<sup>[1]</sup>  $Z_S$  and  $Z_L$  defined in Figure 1.

<sup>[2]</sup> at 3 dB gain compression.

<sup>[2]</sup> at 3 dB gain compression.



**Definition of transistor impedance** Fig 1.

## 7.3 VBW in Doherty operation

The BLC8G27LS-140AV shows 110 MHz (typical) video bandwidth in Doherty demo board in 2600 MHz at  $V_{DS}$  = 28 V;  $I_{Dq}$  = 320 mA and  $V_{GS(amp)peak}$  = 0.6 V.

#### 7.4 Test circuit

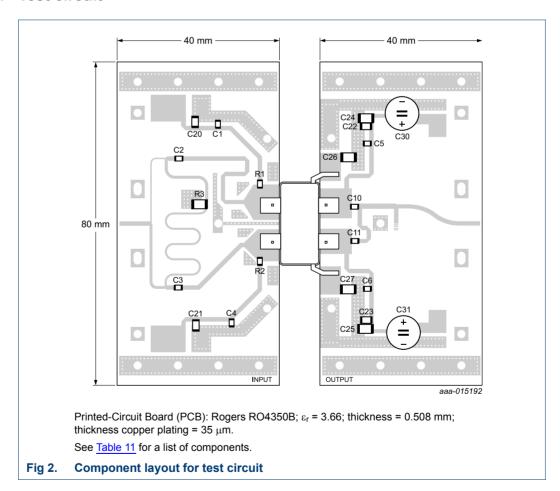


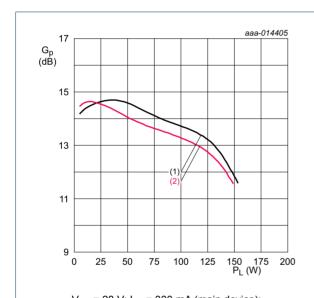
Table 11. List of components

See Figure 2 for component layout.

Component	Description	Value	Remarks
C1, C2, C3, C4, C5, C6	multilayer ceramic chip capacitor	11 pF	
C10	multilayer ceramic chip capacitor	3.3 pF	
C11	multilayer ceramic chip capacitor	9.1 pF	
C20, C21, C22, C23	multilayer ceramic chip capacitor	1 μF, 50 V	
C24, C25, C26, C27	multilayer ceramic chip capacitor	10 μF, 50 V	
C30, C31	electrolytic capacitor	2200 μF, 50 V	
R1, R2	SMD resistor	4.3 Ω	SMD 0805
R3	wire resistor	50 Ω	SMD 2512

## 7.5 Graphical data

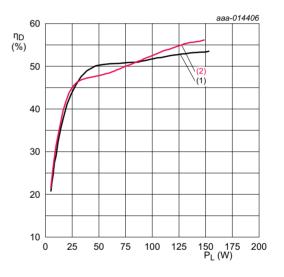
#### 7.5.1 Pulsed CW



 $V_{DS}$  = 28 V;  $I_{Dq}$  = 330 mA (main device);  $V_{GS(amp)peak}$  = 0.55 V;  $t_p$  = 100  $\mu$ s;  $\delta$  = 10 %.

- (1) f = 2496 MHz
- (2) f = 2690 MHz

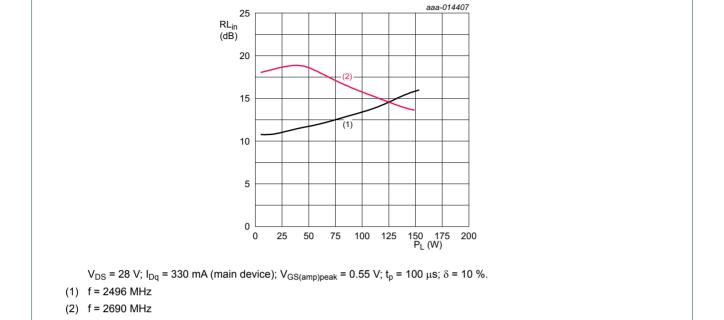
Fig 3. Power gain as a function of output power; typical values



$$\begin{split} &V_{DS} = 28 \text{ V; } I_{Dq} = 330 \text{ mA (main device);} \\ &V_{GS(amp)peak} = 0.55 \text{ V; } t_p = 100 \text{ } \mu\text{s; } \delta = 10 \text{ } \%. \end{split}$$

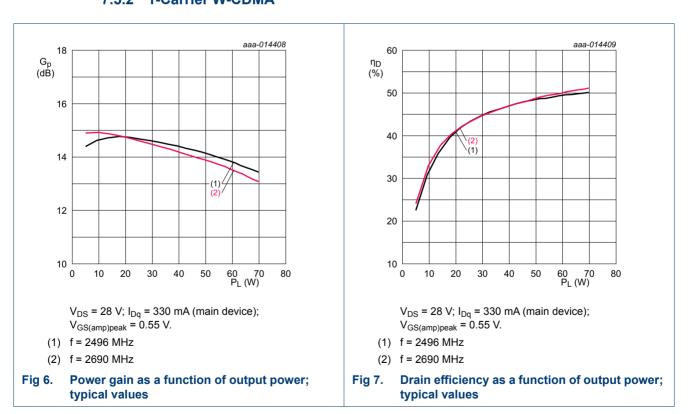
- (1) f = 2496 MHz
- (2) f = 2690 MHz

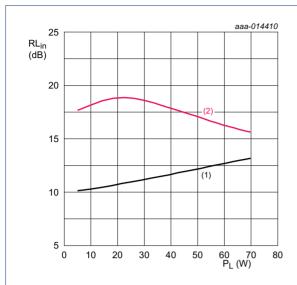
Fig 4. Drain efficiency as a function of output power; typical values



#### 7.5.2 1-Carrier W-CDMA

Fig 5. Input return loss as a function of output power; typical values

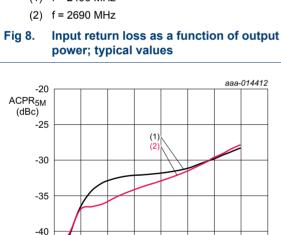




 $V_{DS}$  = 28 V;  $I_{Dq}$  = 330 mA (main device);  $V_{GS(amp)peak} = 0.55 \text{ V}.$ 

(1) f = 2496 MHz

power; typical values



 $V_{DS}$  = 28 V;  $I_{Dq}$  = 330 mA (main device);  $V_{GS(amp)peak} = 0.55 V.$ 

40

(1) f = 2496 MHz

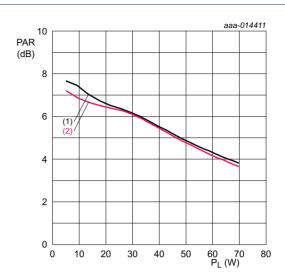
10 20 30

-45

-50

(2) f = 2690 MHz

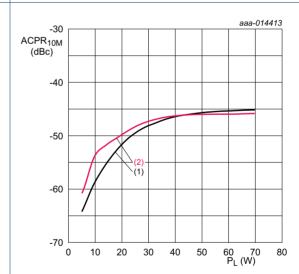
Fig 10. Adjacent channel power ratio (5 MHz) as a function of output power; typical values



 $V_{DS}$  = 28 V;  $I_{Dq}$  = 330 mA (main device);  $V_{GS(amp)peak} = 0.55 V.$ 

- (1) f = 2496 MHz
- (2) f = 2690 MHz

Fig 9. Peak-to-average power ratio as a function of output power; typical values



 $V_{DS}$  = 28 V;  $I_{Dq}$  = 330 mA (main device);  $V_{GS(amp)peak} = 0.55 V.$ 

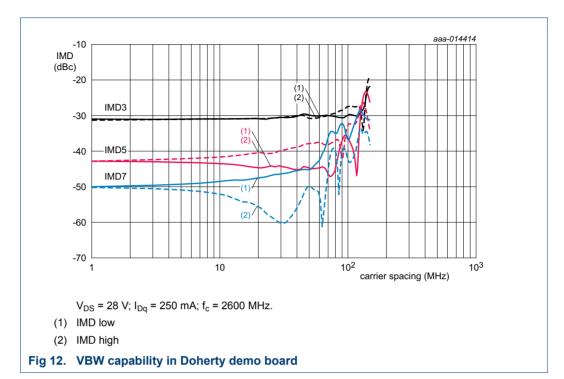
- (1) f = 2496 MHz
- (2) f = 2690 MHz

Fig 11. Adjacent channel power ratio (10 MHz) as a function of output power; typical values

80

60 70 P<sub>L</sub> (W)

#### 7.5.3 2-Tone VBW



## 8. Package outline

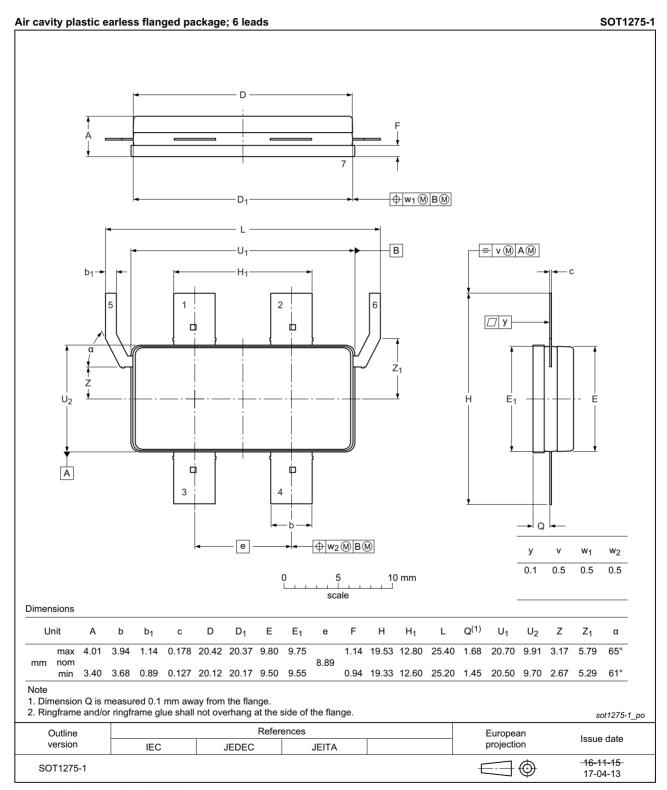


Fig 13. Package outline SOT1275-1

## 9. Handling information

#### **CAUTION**



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 12. ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C2A [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	2 [2]

<sup>[1]</sup> CDM classification C2A is granted to any part that passes after exposure to an ESD pulse of 500 V, but fails after exposure to an ESD pulse of 750 V.

### 10. Abbreviations

Table 13. Abbreviations

Acronym	Description
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
LTE	Long Term Evolution
MTF	Median Time to Failure
PAR	Peak-to-Average Ratio
SMD	Surface Mounted Device
VBW	Video BandWidth
VSWR	Voltage Standing Wave RAtio
W-CDMA	Wideband Code Division Multiple Access

## 11. Revision history

Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLC8G27LS-140AV v.4	20170524	Product data sheet	-	BLC8G27LS-140AV v.3
Modifications:	Figure 13 or	page 10: updated package ou	tline drawing SOT12	75-1
BLC8G27LS-140AV v.3	20161202	Product data sheet	-	BLC8G27LS-140AV v.2
BLC8G27LS-140AV v.2	20150901	Product data sheet	-	BLC8G27LS-140AV v.1
BLC8G27LS-140AV v.1	20141106	Product data sheet	-	-

BLC8G27LS-140AV

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<sup>[2]</sup> HBM classification 2 is granted to any part that passes after exposure to an ESD pulse of 2000 V, but fails after exposure to an ESD pulse of 4000 V.

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#### 12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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# **BLC8G27LS-140AV**

**Power LDMOS transistor** 

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